



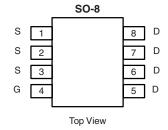
N-Channel 100-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
100	0.034 at V _{GS} = 10 V	6.9		
	0.040 at V _{GS} = 6.0 V	6.4		

FEATURES

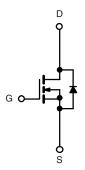
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFETs
- 175 °C Maximum Junction Temperature
- PWM Optimized
- Compliant to RoHS Directive 2002/95/EC





Ordering Information: Si4484EY-T1-E3 (Lead (Pb)-free)

Si4484EY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T	_A = 25 °C, unle	ss otherwise r	noted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	100		V
Gate-Source Voltage		V _{GS}	± 20		
Continuous Dunin Courset /T 475 90\8	T _A = 25 °C	I-	6.9	4.8	٨
Continuous Drain Current (T _J = 175 °C) ^a	T _A = 85 °C	- I _D	5.4	3.7	
Pulsed Drain Current		I _{DM}	30		Α
Avalanche Current	L = 0.1 mH	I _{AR}	25		
Repetitive Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 min	E _{AR}	3	31	mJ
Continuous Source Current (Diode Conduction) ^a		I _S	3.1	1.5	Α
Mariana Pana Pinatanting	T _A = 25 °C	P _D	3.8	1.8	W
Maximum Power Dissipation ^a	T _A = 85 °C] 'D	2.3	1.1	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 t	to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Marrian una lumation ta Analismati	t ≤ 10 s	R_{thJA}	33	40	
Maximum Junction-to-Ambient ^a	Steady State	' 'thJA	70	85	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	17	21	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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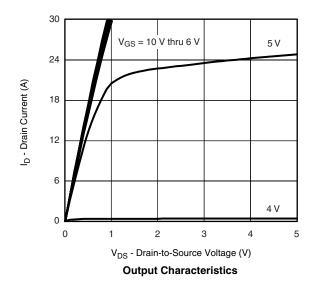
SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	ditions Min.		Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zara Cata Valtaga Drain Current	1	V _{DS} = 80 V, V _{GS} = 0 V	V _{DS} = 80 V, V _{GS} = 0 V		1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 80 V, V _{GS} = 0 V, T _J = 85 °C			20	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	30			Α	
D : 0	D	V _{GS} = 10 V, I _D = 6.9 A		0.028	0.034	0	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 6.0 \text{ V}, I_D = 6.4 \text{ A}$		0.032	0.040	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 6.9 A		25		S	
Diode Forward Voltage ^a	V_{SD}	I _S = 3.1 A, V _{GS} = 0 V		0.8	1.2	V	
Dynamic ^b							
Total Gate Charge	Q_g			24	30		
Gate-Source Charge	Q_{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 6.9 \text{ A}$		7.6		nC	
Gate-Drain Charge	Q_{gd}			5.4		1	
Gate Resistance	R_{g}		0.5	1.25	2.2	Ω	
Turn-On Delay Time	t _{d(on)}			16	30		
Rise Time	t _r	V_{DD} = 50 V, R_L = 50 Ω		10	20		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 1 \text{ A, } V_{GEN} = 10 \text{ V, } R_g = 6 \Omega$		35	70	ns	
Fall Time	t _f			20	40		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 3.1 A, dI/dt = 100 A/μs		50	80		

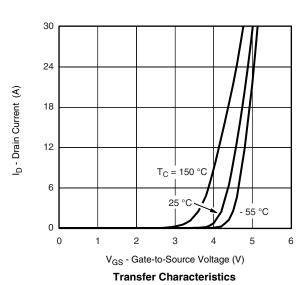
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



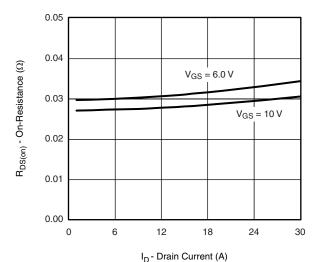




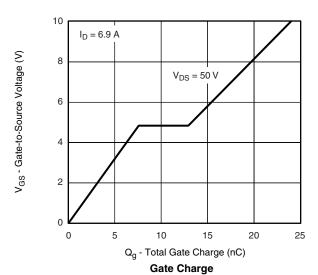


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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



On-Resistance vs. Drain Current



T_J = 175 °C

T_J = 175 °C

T_J = 25 °C

T_J = 25 °C

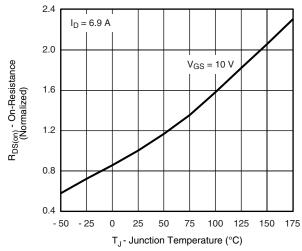
V_{SD} - Source-to-Drain Voltage (V)

Source-Drain Diode Forward Voltage

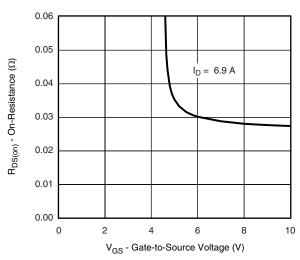
2500 2000 C_{iss} C - Capacitance (pF) 1500 1000 500 C_{rss} $\mathsf{C}_{\mathsf{oss}}$ 0 0 10 20 30 40 50

V_{DS} - Drain-to-Source Voltage (V) **Capacitance**





On-Resistance vs. Junction Temperature



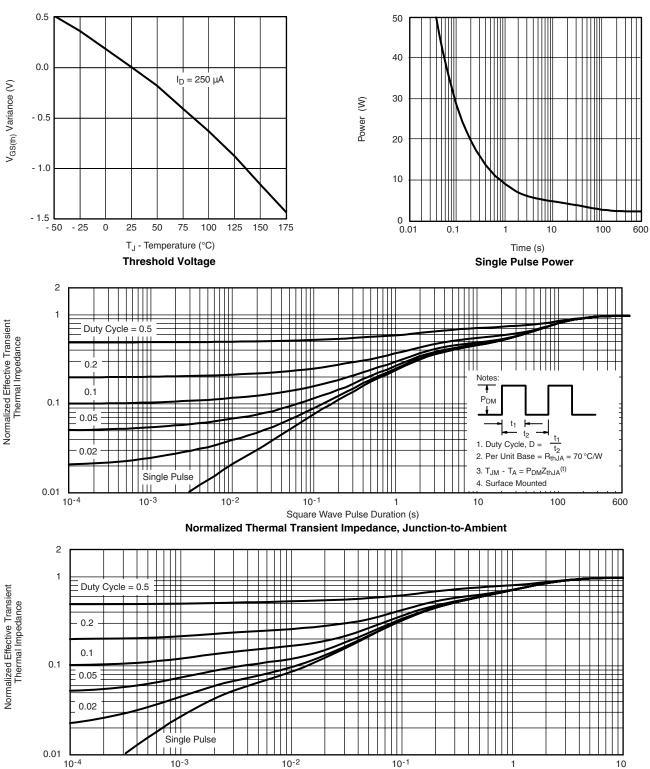
On-Resistance vs. Gate-to-Source Voltage

I_S - Source Current (A)

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



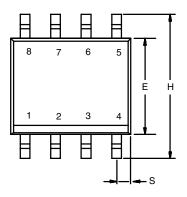
Square Wave Pulse Duration (s)

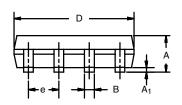
Normalized Thermal Transient Impedance, Junction-to-Foot

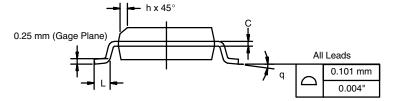
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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIM	IETERS	INC	HES		
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
Е	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I. 11-Sep-06						

DWG: 5498

Document Number: 71192 www.vishay.com 11-Sep-06

APPLICATION NOTE



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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